

Application Manual

Real Time Clock Module **RX411CE**

Product name	Product number				
RX4111CE A	X1B000431000115				
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Low Power Real Time Clock Module with SPI-Bus Interface and Time Stamp Function

RX4111CE

- Built-in frequency adjusted 32.768 kHz crystal unit
- Interface Type
 SPI-Bus 4 wire, 4 MHz Max.
- Low current consumption at backup: 100 nA Typ. / 3.0 V
- Wide operating voltage range : 1.6 V to 5.5 V
- Wide time-keeper voltage range : 1.1 V to 5.5 V
- Auto power switching function
- : Automatically switches to backup power supply by monitoring the V_{DD} voltage.
- Time stamp function

Alarm interruption

- : 8 times time-stamp,1/256 seconds with many selectable trigger.
- Time stamp memory can be used as users memory; 512 bit, 64 word x 8 bit
 - : Day, date, hour, minute, second
- The various functions include full calendar, seconds alarm, wake-up timer, and 32.768 kHz output
- Self monitoring function : Voltage detection, Crystal oscillation stop, etc.

1. Overview

RX4111CE is a real-time clock module with integrated 32.768 kHz crystal oscillator and SPI-Bus interface. In addition to providing a calendar (year, month, date, day, hour, minute, second), this module provides other functions including timestamp from 1/1024 second to year, alarm, wake-up timer, time update interruption, and 32.768 kHz output. Time stamp function can record maximum of 8 events. Using the backup battery switch control function and the interface power supply input pin, RX4111CE can support various power supply circuits. All of the functions mentioned above are offered in a thin and compact 3.2 x 2.5 ceramic package which could be used in various applications requiring small footprints.

2. Block Diagram



Figure 1 Block Diagram

3. Terminal Description

3.1. Terminal Connections



Figure 2 Package Pin Layout

3.2. Pin Functions

Table	1	Pin	Descri	ption

Signal name	I/O	Function
CE	Input	Chip enables input pin (SS) Should be held high to allow access to the CPU. Incorporates a pull-down resistor
CLK	Input	Serial clock input pin (SCLK)
DI	Input	Data input pin (MOSI)
DO	Output	Data output pin (MISO)
FOUT	Output	Frequency output pin (CMOS) (frequency selection: 32.768 kHz, 1024 Hz, 1 Hz) When output is stopped, the FOUT pin is High impedance.
/INT	Open-Drain Output	This pin is used to output alarm signals, timer signals, time update signals, and other signals. This pin is an N-ch open drain
V _{DD}	_	Power-supply pin Possible to supply different voltage from V _{IO}
V _{IO}	-	Interface power supply pin Input to supply the voltage same as a host
VBAT	_	This is a power supply pin for backup battery Connect an EDLC, a secondary battery, a primary battery In the backup voltage range, supplied to IC, from this pin
GND	_	Ground pin

Note:

Be sure to connect a bypass capacitor rated at least 0.1 μF between V_{DD} and GND.

For the input terminals, it is permitted for the input to be 5.5 V regardless of the V_{10} voltage. For the Open-Drain pin, it is permitted for the pull-up to be 5.5 V regardless of the V_{10} voltage.

When FOUT or INT is not used, be left open in these pins. It doesn't need pull-Up/Down resistor.

4. Connection Example

4.1. Battery Switchover Connection Examples

Note. When connecting an outside power supply or a large-sized battery to V_{BAT}, Install bypass capacitors more than 0.1 μ F in a V_{BAT} terminal if necessary. As for each of bypass-capacitor, Install nearest in each of pin as much as possible.

EX.1 V_{IO} and V_{DD} are different.

Ex.2 V_{IO} and V_{DD} are the same.



Figure 3 Circuit Ex.1

Figure 4 Circuit Ex.2

3.3 V

Ex.3 Connecting a Non RE-Chargeable battery

Ex.4 Not using power-switch function



 V_{IO} INIEN = 0 SWSEL1 = 1 SWSEL0 = 0 V_{DD} T_{DD} T_{DD} T_{DD} T_{DD}

Figure 6 Circuit EX.4

5. External Dimensions / Marking Layout

5.1. External Dimensions



Figure 7 External dimensions

5.2. Marking Layout



Figure 8 Marking layout

6. Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

				GND = 0 V
Item	Symbol	Condition	Rating	Unit
Supply voltage	V _{DD}	_	-0.3 ~ +6.5	V
Backup supply voltage	V _{BAT}	_	-0.3 ~ +6.5	V
Interface supply voltage	V _{IO}	_	-0.3 ~ +6.5	V
Input voltage	V _{IN}	CE, CLK, DI	-0.3 ~ +6.5	V
Output voltage 1	V _{OUT1}	/INT	-0.3 ~ +6.5	V
Output voltage 2	V _{OUT2}	FOUT, DO	-0.3 ~ VIO+0.3	V
Storage temperature	Тѕтс	When stored separately, without packaging	–55 to +125	°C

7. Recommended Operating Conditions

Table 3 Recommended Operating Conditions Unless otherwise specified, $GND = 0 \text{ V}$, Ta = -40 °C to +85 °C							
Item	Symbol	Condition	Min.	Тур.	Max.	Unit	
Operating supply voltage	V _{DD}	Normal operation mode (V _{DD})	1.25	3.0	5.5	V	
Interface supply voltage	Vio	$V\text{DD}{=}1.6V\sim5.5V$	1.6	3.0	5.5	V	
Clock supply voltage	V _{CLK}	Backup operation mode (V_{BAT})	1.1	3.0	5.5	V	
Operating temperature	T_use	No condensation	-40	+25	+85	°C	

Minimum value of Clock supply voltage VCLK is the lower supply voltage limit till which the RTC can assure the clock to run. For proper initialization of the RTC RX4111 it is necessary that V_{DD} voltage exceeds 1.6V at power up.

8. Frequency Characteristics

Table 4 Frequency Characteristics

Unless otherwise specified, $V_{BAT} = V_{DD} = V_{IO} = 1.6V \sim 5.5$ V, Ta = -40 °C \sim +85 °C
--

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Oscillation Frequency	fo			32.768		kHz
Frequency Tolerance	∆f/f	Ta = +25 °C V _{DD} = 3.0 V		x : ± 11.5 */ 8 : ± 23.0 */		× 10 ⁻⁶ × 10 ⁻⁶
Frequency/voltage characteristics	f/V	Ta = +25 °C V _{DD} = 1.1 V ~ 5.5 V	-2		+2	\times 10 ⁻⁶ / V
Frequency/ Temperature characteristics	fo-T _C	Ta = -20 °C ~ +70 °C V _{DD} = 3.0 V; +25 °C reference	-120		+10	× 10 ⁻⁶
Oscillation Start-up time	t _{STA}	$V_{DD} = 1.6 \text{ V} \sim 5.5 \text{ V}$			1.0	S
Aging *3	fa	Ta = +25 °C, V _{DD} = 3.0 V; First year	-5		+5	× 10 ⁻⁶ / year

 *1 Equivalent to ±30 seconds per month deviation.

 *2 Equivalent to ±60 seconds per month deviation. *3 Aging stability is estimated from environmental reliability tests; expected amount of the frequency variation. This does not intend to guarantee the product-life cycle.

9. Electrical Characteristics

9.1. DC characteristics

9.1.1 DC characteristics

Table 5 DC characteristics

Item	Symbol	Condition			Min.	Тур.	Max.	Unit
Current consumption 1	I _{DD}	$\begin{array}{l} CE = Low, \\ FOUT = OFF, /INT = OFF, \\ V_{DD} = V_{IO} = 3.0 \ V \\ INIEN = 0b \end{array}$				100	450	nA
Current consumption 2	_{32k}	$CE = LowFOUT = 32.768 \text{ kHz}, /INT = OFFV_{DD} = V_{IO} = 3.0 \text{ V}FOUT pin CL = 15 pFINIEN = 0b$				2.0	3.0	μΑ
Current Consumption 3	Іват	CE = Lo V _{BAT} = 3.		V _{IO} = 0.0 V		110	450	nA
Detection voltage of V _{DD} rise up	+Vdet1	Switch v	oltage of V	/dd from VBAT	1.25	1.35	1.45	V
Detection voltage of V _{DD} fall down	-Vdet1	Switch v	oltage of ∖	/BAT from VDD	1.20	1.30	1.40	V
High Input voltage	VIH		CE, CLI	K, DI	$0.8\times V_{\text{IO}}$		5.5	V
Low Input voltage	VIL		CE, CLI	K, DI	GND - 0.3		$0.2\times V_{\text{IO}}$	V
	V _{OH1}			V, I _{OH} = -1 mA	4.5		5.0	
High Output voltage	Voh2	FOUT, DO	V10 = 3.0	V, I _{OH} = -1 mA	2.2		3.0	V
	V _{OH3}		V _{IO} = 3.0	V, І _{ОН} =-100 µА	2.9		3.0	
	V _{OL1}		V _{IO} = 5.0	0 V, Io∟=1 mA	GND		GND+0.5	
-	V _{OL2}	FOUT, V _{IO} = 3	V _{IO} = 3.0) V, I _{OL} =1 mA	GND		GND+0.8	V
Low Output voltage	V _{OL3}		V _{IO} = 3.0	V, I _{OL} =100 μA	GND		GND+0.1	
-	V _{OL4}	/INT	V _{IO} = 5	V, I _{OL} =1 mA	GND		GND+0.25	V
-	V _{OL5}	/1111		V, IoL = 1 mA	GND		GND+0.4	v
Input lookage ourrent	Ilk		Exclude VIN = VIO 0		-0.1		0.1	٨
Input leakage current	ILKPD		CE, VIN =		-0.1		0.1	μΑ
Output leakage current	loz	Outpu	FOUT, I ut voltage =	DO, = V _{IO} or GND	-0.1		0.1	μΑ
V _{DD} and V _{BAT} SW = OFF leak current	Isw	$V_{BAT} = 3.0 V, V_{DD} = 0.0 V$					50	nA
V_{BAT} and V_{DD} SW = ON resistance	I _{SWON1}				133	-	800	μA
Insuit David		С	Epin	V10 = 5 V	75	150	300	1.0
Input Resistance	Rdwn		$V_{IO} = 3 V$		150	300	600	kΩ

9.1.2 Chargeable Current Characteristics

Chargeable current characteristics for the re-chargeable battery depends on the ON resistance of SW and blow graphs show the voltage dependence of the charge current.

25 °C condition. Horizontal Axis: Vdef (V_{DD} -V_{BAT}), Vertical Axis: Charge current (Ichg)





Figure 9 Chargeable current of VBAT (VDD = 3.0 V)

Figure 10 Chargeable Current of VBAT (VDD = 5.5V)



Figure 11 Circuit of charge to Re-chargeable Battery

9.1.3 Reference Value of Switching Element

Item	Characteristics	Condition
Current tolerance	40 mA Max.	SW = ON +25 °C
Diode Vf	0.60 V / 1 mA Typ. 0.85 V / 10 mA Typ.	V _{DD} = 3.0 V, +25 °C
Diode IR	5 nA (Max.)	VR = 5.5 V, -40 °C ~ +85 °C

Table 6 Reference value of switching element

Charge current into V_{BAT} should be less than 40 mA.

9.2. AC characteristics

9.2.1. AC Characteristics (1)

		Unless otherw	ise specified	d, GND =	0 V, Vio =	1.6 V ~ 5.	5 V, Ia = -	40 °C ~ -	⊦85 °C
ltem	Symbol	Condition	V _{DD} = 1.8 V	/ ± 0.2 V	$V_{DD} = 3.0$	V ± 10 %	$V_{DD} = 5.0$	V ± 10 %	Unit
	<i>cjc.</i>	•••••	Min.	Max.	Min.	Max.	Min.	Max.	•
CLK clock cycle	t _{CLK}		500	—	332	—	250	—	ns
CLK H pulse width	t _{WH}		250	-	166	-	125	—	ns
CLK L pulse width	t _{WL}		250	-	166	-	125	—	ns
CLK rise and fall time	t _{RF}		-	100	—	50		40	ns
CLK setup time	t _{CLKS}		50	-	30	_	30	_	ns
CE setup time	t _{CS}		200	-	150	-	130	—	ns
CE hold time	t _{CH}		400	-	200	-	100	—	ns
CE recovery time	t _{CR}		300	-	200	-	150	—	ns
CE rise and fall time	t _{CERF}		-	100	-	50		40	s
Write data setup time	t _{DS}		100	-	50	_	40	—	ns
Write data hold time	t _{DH}		100	-	50	_	40	—	ns
Read data delay time	t _{RD}	CL = 50 pF	-	200	—	150	_	110	ns
DO output disable time	t _{RZ}	CL = 50 pF RL = 10 kΩ	_	200	_	120	-	110	ns
DI/DO conflict avoiding time	t _{zz}		0	_	0	_	0	_	ns

Table 7 AC Characteristics

1. Please refer to a standard of V_{IO} = 1.8 V \pm 0.2 V for V_{IO} = 2.0 V ~ 2.7 V.

2. Please refer to a standard of V_{IO} = 3.0 V ± 10 % for V_{IO} = 3.3 V \sim 4.5 V.



Figure 12 SPI-Bus Timing Chart

Note: When writing data, it overwrites the data at CLK rise after transmitting 8 bits of data. If communication is interrupted Before receiving data, data will not be written.

9.2.2. AC Characteristics (2)

	Ur	less otherwise specified	d、GND=0 V	, $V_{IO} = 1.6 V$	$\sim 5.5 \mbox{ V}$, Ta	= −40 °C ~ +	-85 °C
Item	Symbol	Condition	Min.	Тур.	Max.	Unit	
FOUT symmetry	SYM	50 % V _{IO} Level	40		60	%	

Table 8 FOUT symmetry

10. Matters that demand special attention on use

10.1. Characteristic for the Fluctuation of the Power Supply

 t_{R1} is needed for a proper power-on reset. If this power-on condition cannot be kept, it is necessary to reset the device by means of a software command.

After power-OFF, keep $V_{DD} = V_{BAT} = GND$ for more than 10 seconds for a proper power-on reset. When it is impossible, please initialize the RTC by software.

The backup period against this standard does not indicate the noise characteristics with respect to the power supply. The backup period should be long enough (60 seconds or more).



		Table 9 Fower up down t		1131103			
Item	Symbol	Condition		Min.	Тур.	Max.	Unit
Initial power supply rise	4		5 V	0.1	-	10	ms / V
time	t _{R1}	From GND to $V_{DD} = +V_{DET1}$	3 V	0.5	-	10	ms / V
Access wait time (Initial power on)	t _{CL}	After arrival to $V_{DD} = 1.6$ \	/	30	-	-	ms
Backup switchover start wait time	tcD	After the access end		0	-	-	ms
Power supply fall time	t⊦	From V _{DD} to V _{DD} = -V _{DET1}		1	-	-	ms / V
Power supply rise time (Recovery from Backup)	t _{R2}	Recovery to the operating vol	tage	0.1	-	-	ms / V
Access wait time (Recovery from Backup)	tcu	The time from Recovery from Backup to access start	m	40	-	-	ms

Table 9 Power up down characteristics

*1 Power-on reset is performed at the rising edge of V_{BAT} or V_{DD} .

*2 Since the V_{DD} voltage monitoring (+V_{DET1}) during backup is intermittent operation (31.25 ms) , a delay occurs after V_{DD} reaches +V_{DET1} until the power supply switches.

*3 For internal initialization, the V_{DD} voltage at the initial power-on must be increased to 1.6 V or more.

10.2. V_{DD} and CE Timing at Power On

When the power is turned to ON, use with CE = Low, V_{CL} V in the diagram as illustrated in the following timing chart.



Figure 14 V_{DD}, CE sequence

		Table 10 CE Timing		
Item	Symbol	Remark	Specification	Unit
CE voltage when power is turned to ON	Vcl	CE impressed voltage until V_{DD} = 1.6 V	0.3 Max.	V
$CE = V_{CL}V$ time when power is turned to ON	tc∟	Time to maintain CE = V_{CL} until V_{DD} = 1.6 V	40 Min.	ms

10.2. Restrictions on Access Operations During Power-on Initialization and Recovery from Backup

Because most of RTC registers are synchronized with the oscillation clock of the built-in crystal oscillator, the RTC does not work normally without the integrated oscillator having stabilized. Please initialize the RTC at the time the power supply voltage returns (VLF = 1) after the oscillation has stabilized (after oscillation start time t_{STA}). If intending to access the RTC after the main supply voltage returns, please note following points:



Figure 15 Oscillation start time chart (Power initial supply)

· Recovery from Backup



Figure 16 Recovery from Backup

10.3. Reset by Software

Software sequence for generating Power-on-reset

- 1) Power ON
- 2) Wait more than 40 ms. *1 *2
- 3) Dummy readout
- 4) Confirm VLF-bit = 1.
- 5) Write 00h Address: Bank3 - 2h INIEN = 0b
- Write 80h Address: Bank3 Fh TEST = 1 6) *3
- 7) Write 6Ch Address: Bank5 - 0h
- Write 03h Address: Bank5 1h 8)
- 9) Write 10h Address: Bank5 - 2h
- Write 20h Address: Bank5 3h 10)
- Wait more than 2 ms. TEST-bit is reset automatically. *4 11)
- *1 When 40 ms waiting time is so long time in your system, an another method. Jump to step3 from step1. At step4, when VLF is 1, write 0 to VLF. While VLF is 1, repeat reset to VLF and verify VLF is 0.
 - If VLF is cleared to 0, jump to step5. In this method, it have possibility this sequence is short than 40 ms.
 - After 40 ms, when VLF doesn't reset to 0, go to step5.
- *2 Dummy reading. Any address is acceptable.
- *3 Should be execute this command even if VLF is 0. Even if VLF is 1, it available after step5.
- *4 2ms is time for RESET processing.
- Note: Except using this RESET sequence, never write 1 to a TEST- bit.

11. Reference information

11.1. Reference Data



12. Application notes

1) Notes on handling

This module uses a C-MOS IC to realize low power consumption. Carefully note the following cautions when handling.

(1) Static electricity

While this module has built-in circuitry designed to protect it against electrostatic discharge, the chip could still be damaged by a large discharge of static electricity. Containers used for packing and transport should be constructed of conductive materials. In addition, only soldering irons, measurement circuits, and other such devices which do not leak high voltage should be used with this module, which should also be grounded when such devices are being used.

(2) Noise

If a signal with excessive external noise is applied to the power supply or input pins, the device may malfunction or "latch up." In order to ensure stable operation, connect a filter capacitor (preferably ceramic) of greater that 0.1 μ F as close as possible to the power supply pins. Also, avoid placing any device that generates high level of electronic noise near this module.

(3) Voltage levels of input pins

When the voltage of out of the input voltage specifications range input into an input terminal constantly, a penetration electric current occurs. Thus, current consumption increases very much. This causes Latch-up, and there is the case that, as a result, a built-in IC is destroyed. Please use an input terminal according to input voltage specifications. Furthermore, please input the Vio or GND most recent voltage as much as possible.

(4) Handling of unused pins

Disposal of unused input terminals. When an input terminal is open state, it causes increase of a consumption electric current and the behavior that are instability. Please fix an unused input terminal to the voltage that is near to Vio or GND.

2) Notes on packaging

(1) Soldering heat resistance.

If the temperature within the package exceeds +260 °C, the characteristics of the crystal oscillator will be degraded and it may be damaged. The reflow conditions within our reflow profile is recommended. Therefore, always check the mounting temperature and time before mounting this device. Also, check again if the mounting conditions are later changed.

(2) Mounting equipment

While this module can be used with general-purpose mounting equipment, the internal crystal oscillator may be damaged in some circumstances, depending on the equipment and conditions. Therefore, be sure to check this. In addition, if the mounting conditions are later changed, the same check should be performed again.

(3) Ultrasonic cleaning

Depending on the usage conditions, there is a possibility that the crystal oscillator will be damaged by resonance during ultrasonic cleaning. Since the conditions under which ultrasonic cleaning is carried out (the type of cleaner, power level, time, state of the inside of the cleaning vessel, etc.) vary widely, this device is not warranted against damage during ultrasonic cleaning.

(4) Mounting orientation

This device can be damaged if it is mounted in the wrong orientation. Always confirm the orientation of the device before mounting.

(5) Leakage between pins

Leakage between pins may occur if the power is turned on while the device has condensation or dirt on it. Make sure the device is dry and clean before supplying power to it.

(6) Installation of charged battery.

When a charged backup battery is installed by soldering, battery connection terminal of this device should connect to GND, beforehand.

13. Overview of Functions and Description of Registers

Note: The initialization of the register is necessary about the unused function.

13.1. Overview of Functions

1) Clock functions

This function is used to set and read out second, minute, hour, day, month, last two digits of the year, and date data. Any two-digit year that is a multiple of 4 is treated as a leap year and calculated automatically as such until the year 2099. It corresponds to the writing of 60 seconds for leap second correction.

2) Wake-up Timer Interrupt Function

The Wake-up timer interrupt function generates an interrupt event periodically at any Wake-up set between 244.14 μs and 32 years.

When an interrupt event is generated, the /INT pin goes to low level and 1 is set to the TF bit to report that an event has occurred.

It can use Wake-up timer interrupt function as Long-Timer or Wake up timer.

This function measures the operation time on the main power supply and the operation time on the backup power supply and can automatically sum them up.

3) Alarm Interrupt Function

The alarm interrupt function generates interrupt events for alarm settings such as date, day, hour, minute, and second settings. When an interrupt event occurs, the AF bit value is set to 1 and the /INT pin goes to low level to indicate that an event has occurred.

4) Voltage Drop Detection Function

This is a function to detect a drop in V_{DD} voltage.

It is possible to judge whether the timekeeping contents are valid, such as when the initial power is turned on or when the power supply voltage drops.

When a voltage drop is detected, the device enters the initial state (reset state) by the power-on reset function.

5) Frequency Stop Detection Function

This flag bit indicates the retained status of clock operations or internal data. Its value changes from 0 to 1 when data loss might have occurred due to a low supply voltage.

6) Clock Output Function

A clock with the same frequency (32.768 kHz) as the built-in crystal resonator can be output from the FOUT pin. Output could also be 1 Hz, or 1024 Hz.

7) Time Stamp Function

Data can be recorded from 1/10024 second digit to year digit.

8) User RAM

RAM register is read/write accessible for any data.

Built-in 8bit × 64word (512bit) RAM

When not use Timestamp function, it can use for users memory.

13.2. Register Table The target register is selected and accessed with the first 4-bit mode setting code of communication.

-			Table 11 SP	I-Bus 4bits Re	egisters		
Mode	Bank1	Bank2	Bank3	Bank4	Bank5	Bank6	Bank7
Read	9h	Ah	Bh	Ch	Dh	Eh	Fh
Write	1h	2h	3h	4h	5h	6h	7h

13.2.1. Register Table

			Table ²	12 Registe	Table 1	-	-		,
Bank1	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Address	T difetion	5107	DIEO	DILO		DR O	5112		DIT U
0h	SEC	z	40	20	10	8	4	2	1
1h	MIN	z	40	20	10	8	4	2	1
2h	HOUR	z	z	20	10	8	4	2	1
3h	WEEK	z	6	5	4	3	2	1	0
4h	DAY	z	z	20	10	8	4	2	1
5h	MONTH	z	z	z	10	8	4	2	1
6h	YEAR	80	40	20	10	8	4	2	1
7h	MIN Alarm	AE	40	20	10	8	4	2	1
8h	HOUR Alarm	AE	•	20	10	8	4	2	1
9h	WEEK Alarm	AE	6	5	4	3	2	1	0
911	DAY Alarm	AE	•	20	10	8	4	2	1
Ah	Timer Counter 0	128	64	32	16	8	4	2	1
Bh	Timer Counter 1	32768	16384	8192	4096	2048	1024	512	256
Ch	Timer Counter 2	8388608	4194304	2097152	1048576	524288	262144	131072	65536
Dh	Extension Register	FSEL1	FSEL0	USEL	TE	WADA		TSEL1	TSEL0
Eh	Flag Register	POR	z	UF	TF	AF	EVF	VLF	XST
Fh	Control Register	z	z	UIE	TIE	AIE	EIE	z	STOP
Bank2	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Address 0h	Time Stome 1/1024S	<u> </u>	<u> </u>					1/512	1/1024
011 1h	Time Stamp 1/1024S	-	- 1/4	- 1/0	-		-	1/128	1/256
	Time Stamp 1/256S	1/2 z	-	1/8	1/16	1/32	1/64		
2h	Time Stamp SEC	z	40	20	10	8	4	2	1
3h	Time Stamp MIN		40	20	10	8	4	2	1
4h	Time Stamp HOUR	z	z	20	10	8	4	2	1
5h	Time Stamp WEEK	z	6	5	4	3	2	1	0
6h	Time Stamp DAY	z	Z	20	10	8	4	2	1
7h	Time Stamp MONTH	Z	Z	Z	10	8	4	2	1
8h	Time Stamp YEAR	80	40	20	10	8	4	2	1
9h	Status Stamp	z	z	•	•	VDET	Z	XST	Z
Ah	No Function	z	z	z	z	z	z	Z	z
Bh	Over Write Control				lo Functio		[OVW	-
Ch	SEC Alarm	AE	40	20	10	8	4	2	1
Dh	Timer Control	z	z	z	Z	TBKON	TBKE	TMPIN	TSTP
Eh	Time Stamp control 0	z	z	z	z	z	z	z	COMTG
Fh	Command Trigger	+				-			1

			Table 13	Register	Table 2				
Bank3 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Oh	No Function	z	z	z	z	z	z	z	z
1h	No Function	z	z	z	z	z	z	z	z
2h	Power Switch Control		INIEN	Z	z		SWSEL0	_	SMPT0
3h	No Function	z	•	Z	Z	•	Z	•	Z
4h	Time Stamp Control 1	z	z	Z	Z	z	EISEL	TSCLR	TSRAM
5h	Time Stamp Control 2	•	z	z	z		EVDET		EXST
6h	Time Stamp Control 3	z	z	z	TSFUL	TSEMP	TSDA2	TSDA1	TSDA0
7h	No Function	z	z	z	•	z	z	z	•
8h to Dh	No Function	z	z	z	z	z	z	z	z
Eh	No Function	-	-	-	-	-	-	-	-
Fh	TEST	TEST	z	z	z	z	z	z	z
			•			-			
Bank4,5,6,7 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	Time stamp 1/256S	1	2	4	8	16	32	64	128
1h	Time Stamp SEC	٠	40	20	10	8	4	2	1
2h	Time Stamp MIN	٠	40	20	10	8	4	2	1
3h	Time Stamp HOUR	٠	•	20	10	8	4	2	1
4h	Time Stamp DAY	٠	•	20	10	8	4	2	1
5h	Time Stamp MONTH	•	•	•	10	8	4	2	1
6h	Time Stamp YEAR	80	40	20	10	8	4	2	1
7h	Status stamp	•	•	•	•	VDET	•	XST	•
8h	Time stamp 1/256S	1	2	4	8	16	32	64	128
9h	Time Stamp SEC	•	40	20	10	8	4	2	1
Ah	Time Stamp MIN	•	40	20	10	8	4	2	1
Bh	Time Stamp HOUR	•	•	20	10	8	4	2	1
Ch	Time Stamp DAY	•	•	20	10	8	4	2	1
Dh	Time Stamp MONTH	•	•	•	10	8	4	2	1
Eh	Time Stamp YEAR	80	40	20	10	8	4	2	1
Fh	Status stamp	•	•	•	•	VDET	•	XST	•

After the initial power-up (from 0 V) or in case the VLF bit returns 1, make sure to initialize all registers, before using the RTC. Be sure to avoid entering incorrect date and time data, as clock operations are not guaranteed when the data or time data is incorrect. Week data is not need care.

The TEST bit is used by the manufacturer for testing. Be sure to write 0 by initializing before using the RTC. Afterward, be sure to set 0 when writing

Any bit marked with "z" should be used with a value of 0 after initialization. Writing 1 is ignored.

Any bit marked with "•" is a RAM bit that can be used to read or write any data.

Write '0' to the "-" mark when writing. The read value is undefined. Please mask the corresponding bit after reading it. The above table shows only the user registers. Due to functional reasons, RTC has different registers not mentioned above table which are programmed by the manufacturer. Please make sure to only access above mentioned user registers. Writing operation is ignored at any bit marked "No Function".

"▲" mark bits are must be cleared to 0. Afterward, be kept in 0, anytime. When writes 1 to "▲", it has possibility of current consumption is increased.

13.2.2. Register Initial value, And Read/Write Operation Table

This value is initialized by power-on reset.

X: Undefined 0 or 1

Initialization by register writing is needed. It is not necessary to initialize time stamp data area.

- 0: Reset state.
- 1: Set state.

Bank 1 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	SEC	0	Х	Х	Х	Х	Х	Х	Х
1h	MIN	0	Х	Х	Х	Х	Х	Х	Х
2h	HOUR	0	0	Х	Х	Х	Х	Х	Х
3h	WEEK	0	Х	Х	Х	Х	Х	Х	Х
4h	DAY	0	0	Х	Х	Х	Х	Х	Х
5h	MONTH	0	0	0	Х	Х	Х	Х	Х
6h	YEAR	Х	Х	Х	Х	Х	Х	Х	Х
7h	MIN Alarm	1	Х	Х	Х	Х	Х	Х	Х
8h	HOUR Alarm	1	Х	Х	Х	Х	Х	Х	Х
9h	WEEK Alarm	1	Х	Х	Х	Х	Х	Х	Х
90	DAY Alarm		Х	Х	Х	Х	Х	Х	Х
Ah	Timer Counter 0	Х	Х	Х	Х	Х	Х	Х	Х
Bh	Timer Counter 1	Х	Х	Х	Х	Х	Х	Х	Х
Ch	Timer Counter 2	Х	Х	Х	Х	Х	Х	Х	Х
Dh	Extension Register	0	0	0	0	0	0	1	0
Eh	Flag Register	1	0	0	0	0	0	1	Х
Fh	Control Register	0	0	0	0	0	0	0	0

Table 1	1 P	anistar	Initial	Value 1	
rapie i	4 66	eaister	mitiai	value I	

Bank 2 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	Time Stamp 1/1024S	0	0	0	0	Х	Х	Х	Х
1h	Time Stamp 1/256S	Х	Х	Х	Х	Х	Х	Х	Х
2h	Time Stamp SEC	0	Х	Х	Х	Х	Х	Х	Х
3h	Time Stamp MIN	0	Х	Х	Х	Х	Х	Х	Х
4h	Time Stamp HOUR	0	0	Х	Х	Х	Х	Х	Х
5h	Time Stamp WEEK	0	Х	Х	Х	Х	Х	Х	Х
6h	Time Stamp DAY	0	0	Х	Х	Х	Х	Х	Х
7h	Time Stamp MONTH	0	0	0	Х	Х	Х	Х	Х
8h	Time Stamp YEAR	Х	Х	Х	Х	Х	Х	Х	Х
9h	Status Stamp	0	0	Х	Х	Х	0	Х	0
Ah	No Function	0	0	0	0	0	0	0	0
Bh	Over Write Control	0	0	0	0	0	0	0	0
Ch	SEC Alarm	0	0	0	0	0	0	0	0
Dh	Timer Control	0	0	0	0	0	0	0	0
Eh	Time Stamp control 0	0	0	0	0	0	0	0	0
Fh	Command Trigger	0	0	0	0	0	0	0	0

		Table 1	5 Register	· Initial Va	lue 2				
Bank 3 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	No Function	0	0	0	0	0	0	0	0
1h	No Function	0	0	0	0	0	0	0	0
2h	Power Switch Control	0	0	0	0	0	1	0	0
3h	No Function	0	Х	0	0	0	0	0	0
4h	Time Stamp Control 1	0	0	0	0	0	0	0	0
5h	Time Stamp Control 2	0	0	0	0	0	0	0	0
6h 7h	Time Stamp Control 3	0	0	0 0	0	1 0	1 0	1	1 0
8h to Dh	No Function No Function	0	0	0	0	0	0	0	0
Eh	No Function	X	X	X	X	X	X	X	X
Fh	TEST	0	0	0	0	0	0	0	0
									-
Bank4,5,6,7 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	Time stamp 1/256S	Х	Х	Х	Х	Х	Х	Х	Х
1h	Time Stamp SEC	Х	Х	Х	Х	Х	Х	Х	Х
2h	Time Stamp MIN	Х	Х	Х	Х	Х	Х	Х	Х
3h	Time Stamp HOUR	Х	Х	Х	Х	Х	Х	Х	Х
7h	Time Stamp DAY	Х	Х	Х	Х	Х	Х	Х	Х
5h	Time Stamp MONTH	Х	Х	Х	Х	Х	Х	Х	Х
6h	Time Stamp YEAR	Х	Х	Х	Х	Х	Х	Х	Х
7h	Status stamp	Х	Х	Х	Х	Х	Х	Х	Х
8h	Time stamp 1/256S	Х	х	Х	Х	Х	Х	Х	х
7h	Time Stamp SEC	Х	Х	Х	Х	Х	Х	Х	Х
Ah	Time Stamp MIN	Х	Х	Х	Х	Х	Х	Х	Х
Bh	Time Stamp HOUR	Х	х	Х	Х	Х	Х	Х	Х
Ch	Time Stamp DAY	Х	х	Х	Х	Х	Х	Х	Х
Dh	Time Stamp MONTH	Х	х	Х	Х	Х	Х	Х	Х
Eh	Time Stamp YEAR	Х	х	Х	Х	Х	Х	Х	Х
Fh	Status stamp	Х	Х	Х	Х	Х	Х	Х	Х

X: Undefined 0 or 1

0: Reset state.

1: Set state.

13.3. Description Of Registers

- 13.3.1. Clock and Calendar Counter (Bank1 1h ~ 6h) This is counter registers from a second to a year. Please refer to [14.1 Clock calendar explanation] for details.
- 13.3.2. Timer Setting and Timer Counter Register (Bank1 Ah ~ Ch) This register is used to set the default (preset) value for the counter. To use the Wake-up timer interrupt function, TE, TF, TIE, TSEL1, TSEL0, TBKON, TBKE, TSTP, TMPIN bits are set and used. When the Wake-up timer interrupt function is not being used, the Wake-up timer control register can be used as a RAM register. In such cases, stop the Wakeup timer function by writing 0 to the TE and TIE bits. Please refer to [14.2. Wakeup Timer Interrupt Function] for the details.
- 13.3.3. Alarm Registers (Bank1 7h ~ 9h, Bank2 Ch) The alarm interrupt function is used, along with the AE, AF, and WADA bits, to set alarms for specified date, day, hour, minute, and second values. Please refer to [14.3. Alarm Interrupt Function] for the details.

- 13.3.4. Function-Related Register (Bank1 1Dh ~ 1Fh)
- FSEL1, FSEL0 bit A combination of the FSEL1 and FSEL0 bits are used to select the frequency to be output. If customer does not use this function, FESL1, FSEL0 should be set to 1. Please refer to 14.6 FOUT Function
- 2) USEL, UF, UIE bit

This bit is used to specify either second update or minute update as the update generation timing of the time update interrupt function. If customer does not use this function, USEL, UIE should be reset to 0. UF do not care. Please refer to [14.4. Update interrupt function] for the details.

- TE, TF, TIE, TSEL1, TSEL0, TSTP, TBKON, TBKE, TMPIN bit These bits are used to control operation of the wake-up timer interrupt function. If customer does not use this function, (TE, TIE, TSTP, TMPIN) should be (0,0,0,0), TSEL1, TSEL0(1,0). TF do not care. Please refer to [14.2 Wake-up timer interrupt function] for the details.
- 4) WADA, AF, AIE bit

These bits are used to control operation of the alarm interrupt function. If customer does not use this function, WADA should be 1, AIE 0. AF do not care. Please refer to [14.3. Alarm interrupt function] for the details.

5) ETS, EVF, EIE bit

These bits are used to control operation of the time stamp function. If customer does not use this function, ETS, EIE should be reset to 0. EVF do not care. Please refer to [14.8. Time Stamp function] for the details.

6) VLF, POR, XST bit

These bits are used to detect RTC inner status and recording. Ex. During power on resetting, lower voltage detection makes VLF bit 1. Please refer to [14.5. RTC inner status detection function] for the details.

7) STOP bit

This bit is to stop a timekeeping operation. In the case of STOP = 1:

All the update of timekeeping (year, month, day, week, hour, minute, second, 1/128 s, 1/512 s) operation and the calendar operation stops. With it, an update interrupt event does not occur at an alarm interrupt and the time stamp data is to be stopping condition.

(Please refer to 14.8.5)

The part of the fixed-cycle timer interrupt function stops.

A count stops the source clock setting of the timer in case of 64 Hz, 1 Hz, 1 min, 1 h.

(In case of 4096 Hz, it does not stop.)

The effect of STOP bit to FOUT functions.

When STOP = 1, 32.768 kHz and 1024 Hz output is possible. But 1 Hz output is disabled.

Switchover function cannot work in order that the V_{DD} voltage drop detection stops even if a main power supply falls.

13.3.5. Power Switching Circuit-Related Register Bank3 02h

- 1) INIEN bit This bit sets power switching operation and SPI-Bus communication stop at backup
- SMPT1, SMPT0 bit This bit sets the intermittent operation active time of the voltage monitoring circuit of the built-in MOS switch.
- SWSEL1, SWSEL0 bit When not using the power switching function, this bit sets the built-in MOS switch.
- 13.3.6. Time stamp-related register Please refer to [13.8. Time stamp function] for the details.
- Time stamp and status record register (Bank2 0h ~ 9h; Bank4, 5, 6, 7 0h ~ Fh) This register records time stamp data from 1/1000 second digit to Year digit and internal state when an event occurs.
- Command trigger Time stamp control register (Bank2 Eh ~ Fh) This register is used when triggering time stamp using SPI-Bus communication access.
- 3) Time stamp trigger control register (Bank3 5h) This register is used to perform time stamp trigger.
- 13.3.7. RAM registers (Bank4, 5, 6, 7) This RAM register is read/write accessible for any data in the range from 0h to Fh.

14. How to use



Figure 18 Basic Function 32.768 kHz oscillation, counter, FOUT

14.1. Clock Calendar Explanation

At the time of a communication start, the Clock & Calendar data are fixed (hold the carry operation), and it is automatically revised at the time of the communication end. Therefore, it recommends that the access to a clock calendar has continuous access by the auto increment function. When reading the current time, do not use the STOP bit (STOP = 0).

Setting example: Sun, 29-Feb-88 17:39:45 (leap year)

		105			i setting i	-7.			
Bank1 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
0h	SEC	0	1	0	0	0	1	0	1
1h	MIN	0	0	1	1	1	0	0	1
2h	HOUR	0	0	0	1	0	1	1	1
3h	WEEK	0	0	0	0	0	0	0	1
4h	DAY	0	0	1	0	1	0	0	1
5h	MONTH	0	0	0	0	0	0	1	0
6h	YEAR	1	0	0	0	1	0	0	0
Nata									

Table 16 Time Calendar setting Ex

Note

With caution that writing non-existent time data may interfere with normal operation of the clock counter Time starts at the moment of STOP bit operation (1 to 0 timing)

14.1.1. Clock Counter

1) [SEC], [MIN] register

These registers are 60-base BCD counters. When update signals were generated from a lower counter, a upper counter is one incremented. At the timing when the lower register changes from 59 to 00, carry is generated to the higher register and thus incremented.

When writing is performed to [SEC] register, Internal-count-down-chain less than one second (512 Hz ~ 1 Hz) is cleared to 0.

2) [HOUR] register

This register is a 24-base BCD counter (24-hour format). These registers are incremented at the timing when carry is generated from a lower register.

- 3) Leap seconds adjustment
- 4) For leap second adjustment, user can write 60 into SEC counter.
 - 1 seconds after, SEC-counter updates to 00. Generally SEC counter updates to 00 from 59.

14.1.2. Week Counter

The day (of the week) is indicated by 7 bits, bit 0 to bit 6.

The day data values are counted as: Day $01h \rightarrow Day 02h \rightarrow Day 04h \rightarrow Day 08h \rightarrow Day 10h \rightarrow Day 20h \rightarrow Day 40h \rightarrow Day 01h \rightarrow Day 02h$, etc.

It is incremented when carry is generated from the HOUR register. This register does not generate carry to a higher register. Since this register is not connected with the YEAR, MONTH and DAY registers, it needs to be set again with the matching day of the week if any of the YEAR, MONTH or DAY registers have been changed.

When not use Week data, It is not necessary for Week register to be initialized.

Do not set 1 to more than one day at the same time.

Table 17 Week Register

Day	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	Data [h]
Sunday	0	0	0	0	0	0	0	1	01 h
Monday	0	0	0	0	0	0	1	0	02 h
Tuesday	0	0	0	0	0	1	0	0	04 h
Wednesday	0	0	0	0	1	0	0	0	08 h
Thursday	0	0	0	1	0	0	0	0	10 h
Friday	0	0	1	0	0	0	0	0	20 h
Saturday	0	1	0	0	0	0	0	0	40 h

Do not set 1 to more than one day at the same time.

14.1.3. Calendar Counter

1) [DAY], [MONTH] resister

The DAY register is a variable (between 28-base and 31-base) BCD counter that is influenced by the month and the leap year. The MONTH register is 12-base BCD counter. when carry is generated from a lower register.

Table 18 DAY, MONTH Register

	Jan.	Feb.	Mar	Apr.	Mav	June	lubz	Aua.	Sep.	Oct.	Nov.	Dec.
	Jan.	rep.	Iviai	Арі.	iviay	Julie	July	Auy.	Sep.	000	INUV.	Dec.
Days Normal year Leap year	31	28 29	31	30	31	30	31	31	30	31	30	31

2) [YEAR] register

This register is a BCD counter for years 00 to 99.

The leap year is automatically determined and influences the DAY register.

This RTC processes following years as leap years: 00,04,08,12, 96.

User software correction is needed in the years 2100, 2200, 2300 as they are common years.

Definition of leap years

Leap year: year divisible by 4, year divisible by 400

Ex. 2000, 2004, 2008, 2012, 2096, 2400, 2800,

Common year: year indivisible by 4, year divisible by 100

Ex. 2001, 2002, 2003, 2005, 2099, 2100, 2200, 2300, 2500,,

14.2. Wake-up Timer Interrupt Function

The Wake-up timer interrupt function generates an interrupt event periodically at any Wake-up set between 244.14 μ s and 31.9 years. It can be paused and can also be used as an accumulate timer. 7.813 ms after the interrupt occurs, the /INT status is automatically cleared (/INT status changes from low-level to Hi-z).

14.2.1. Related Registers For Function Of Wake-up Timer Interrupt Function

			manc-up		inupt neg	13101			
Bank1 Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
А	Timer Counter 0	128	64	32	16	8	4	2	1
В	Timer Counter 1	32768	16384	8192	4096	2048	1024	512	256
С	Timer Counter 2	8388608	4194304	2097152	1048576	524288	262144	131072	65536
D	Extension Register	FSEL1	FSEL0	USEL	TE	WADA		TSEL1	TSEL0
E	Flag Register	POR	z	UF	TF	AF	EVF	VLF	XST
F	Control Register	z	z	UIE	TIE	AIE	EIE	z	STOP
Bank2-D	Timer Control	z	z	z	z	TBKON	TBKE	TMPIN	TSTP

Table 19 Wake-up Timer Interrupt Register

Before setting the operation, clear the TE bit to 0.

When the Wake-up timer function is not being used, the Wake-up Timer Counter0,1 register can be used as a RAM register. In such cases, stop the Wake-up timer function by writing 0 to the TE and TIE bits.

1) Down counter for Wake-up timer (Timer Counter 2, 1, 0)

This register is used to set the default (preset) value for the counter. Any count value from 1 to 16777216 can be set. Be sure to write 0 to the TE bit before writing the preset value.

When TE=0, read out data of timer counter is default (Preset) value. When TE = 1, read out data of timer counter is just counting value. But, when access to timer counter data, counting value is not held.

Therefore, for example, perform twice read access to obtain right data, and a way to adopt the case that two data accorded is necessary.

2) TSEL1, TESL0 bit

The combination of these three bits is used to set the countdown period (source clock) for this function.

-			Jeleci
TSEL1 (bit 1)	TSEL0 (bit 0)	Source clock	Auto release time tRTN
0	0	4096 Hz /Once per 244.14 μs	122 μs
0	1	64 Hz /Once per 15.625 ms	7.813 ms
1	0	1 Hz /Once per second	7.813 ms
1	1	1/60 Hz /Once per minute	7.813 ms

Table 20 TSEL bit Source Clock Select

1) The /INT pin's Auto reset time (tRTN) varies as shown above according to the source clock setting.

2) The first countdown shortens than a source clock.

When selected 4096 Hz / 64 Hz / 1 Hz as a source clock, one period of error occurs at the maximum. When selected 1/60 Hz, 1 Hz of error occurs at the maximum.



Figure 19 Wake-up Timer Initial Sequence (cycle error)

Inside counter block diagram



3) TE bit (Timer Enable)

When TE bit is 0, the default (preset) can be checked by reading this register.

Table 2	1 TE bit	(Timer	Enable)	
				l

TE	Data	Description
	0	Stops Wake-up timer interrupt function. Clearing this bit to zero does not enable the /INT low output status to be cleared (to Hi-z).
Write	1	Starts Wake-up timer interrupt function. The countdown that starts when the TE bit value changes from 0 to 1 always begins from the preset value.

4) TF bit (Timer Flag)

This is a flag bit that retains the result when a Wake-up timer interrupt event is detected.

Table 22 TF bit (Timer Flag)

TF	Data	Description					
Write 0		The TF bit is cleared to zero to prepare for the next status detection Clearing this bit to zero does not enable the /INT low output status to be cleared (to Hi-z).					
	1	Invalid. writing a 1 will be ignored					
	0	-Wake-up timer interrupt events are not detected.					
Read	1	Wake-up timer interrupt events are detected. (Result is retained until this bit is cleared to zero.)					

5) TIE bit (Timer Interrupt Enable)

This bit is used to control output of interrupt signals from the /INT pin when a Wake-up timer interrupt event has occurred.

Table 23 TIE bit (Timer Interrupt Enable)

TIE	Data	Description
Write	0 Write	 When a Wake-up timer interrupt event occurs, an interrupt signal is not generated. When a Wake-up timer interrupt event occurs, the interrupt signal is canceled (/INT status changes from low to Hi-z).
	1	When a Wake-up timer interrupt event occurs, an interrupt signal is generated (/INT status changes from Hi-z to low).

6) TBKON, TBKE bit

This function selects the operation time with the main power supply or the operation time with the backup power supply. The count value is added.

Table 24 TBKON, TBKE (Timer Backup ON, Timer Backup/Normal Enable)

operation	TBKE	TBKON	Description			
0		Х	This setting counts normal mode and backup mode.			
Write	4	0	This setting counts it at time of normal mode (VDD operation)			
		1	This setting counts it at time of backup mode (V _{BAT} operation)			

7) TMPIN bit

The timer interrupt output can be assigned to the /INT or FOUT pin. Since it is an OR output with the FOUT setting, please set the FOUT output setting to FSEL 1, 0 = (1, 1) and OFF the frequency output function.

Table 25 TMPIN bit (Timer Pin)								
TMPIN	Data	Description						
\\/rito	0	Assign output to / INT pin						
Write	1	Assign output to FOUT pin						

Table 25 TMPIN bit (Timer PIN)

8) TSTP bit (Timer Stop)

This bit is used to stop Wake-up timer count down.

_	Table 26 TSTP bit (Timer STOP)								
TE	STOP	TBKE	TSTP	Description					
		0	0	Writing a 0 to this bit cancels stop status (restarts timer counts down). The reopening value of the countdown is a stopping value					
1	0		1	Count stops.					
		1	х	TSTP is invalid. and the count down doesn't stop even if set in TSTP = 1.					
	1	Х	Х	The count stops at the time of the setting of 64 Hz, 1 Hz,1/60 Hz.					
0	Х	Х	Х	It doesn't start counting					

14.2.2. Wake-up Timer Start Timing

The timer source clock selects bits (TSEL1, TSEL0) are also fixed at the rising edge of CLK. The timer countdown starts after the data is fixed at the rising edge of CLK of the 8th data bit (D0).



Figure 21 Wake-up Timer Start Sequence

14.2.3. Interruption period of wake-up Timer.

The combination of the source clock settings and Wake-up timer countdown value sets interrupt interval, as shown in the following examples.

	Source clock								
Timer Counter setting 1 ~ 16777216	4096 Hz TSEL1, 0 = 0, 0	64 Hz TSEL1, 0 = 0, 1	1 Hz TSEL1, 0 = 1, 0	1/60 Hz TSEL1, 0 = 1, 0					
0	_	_	_	_					
1	244.14 μs	15.625 ms	1 s	1 min					
•	•	•	:	:					
410	100.10 ms	6.406 s	410 s	410 min					
:	:	:	:	:					
3840	0.9375 s	60.000 s	3840 s	3840 min					
:	:	•	:	•					
4096	1.0000 s	64.000 s	4096 s	4096 min					
:	:	•	:	•					
16777216	1.13 h	72.81 h	4660 h	31.9 Year					

Table 27 Wake-up Timer Interrupt Cycles

When the all counter value is set to 0b, the timer will not work.





Figure 22 Wake-up Timer Block Diagram



Figure 23 Wake-up Timer Timing Chart

After the interrupt event that occurs when the count value changes from 1h to 0h, the counter automatically reloads the preset value and again starts to count down. (Repeated operation)

The countdown that starts when the TE bit value changes from 0 to 1 always begins from the preset value.

14.3. Alarm Interrupt Function

The alarm interrupt function generates interrupt events for alarm settings such as date, day, hour, minute, and second settings. When an interrupt event occurs, the AF bit value is set to 1 and the /INT pin goes to low level to indicate that an event has occurred.

/INT= Low output when occurs alarm interruption event is not cancelled automatically unless giving intentional cancellation and /INT = Low are maintained.

14.3.1. Related Registers for Alarm Interrupt Functions.

Table 20 Alarm Interrupt Registers									
Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank2 - C	SEC Alarm	AE	40	20	10	8	4	2	1
Bank1 - 7	MIN Alarm	AE	40	20	10	8	4	2	1
8	HOUR Alarm	AE	•	20	10	8	4	2	1
9	WEEK Alarm		6	5	4	3	2	1	0
9	DAY Alarm	AE	•	20	10	8	4	2	1
D	Extension Register	FSEL1	FSEL0	USEL	TE	WADA	•	TSEL1	TSEL0
E	Flag Register	POR	z	UF	TF	AF	EVF	VLF	XST
F	Control Register	z	z	UIE	TIE	AIE	EIE	z	STOP

Table 28 Alarm Interrupt Registers

Before entering settings for operations, it is recommended to first set the AIE bit to 0 in order to avoid inadvertent hardware interrupt at setting.

When the STOP bit value is 1 alarm interrupt events do not occur.

When the alarm interrupt function is not being used, the Alarm registers can be used as a RAM register. In such cases, be sure to write 0 to the AIE bit. When the AIE bit value is 1 and the Alarm registers is being used as a RAM register, /INT may be changed to low level unintentionally.

1) Alarm registers

The second, minute, hour, day and date when an alarm interrupt event will occur is set using this register and the WADA bit.

In the WEEK alarm /Day alarm register, the setting selected via the WADA bit determines whether WEEK alarm data or DAY alarm data will be set. If WEEK has been selected via the WADA bit, multiple days can be set (such as Monday, Wednesday, Friday, Saturday).

In case AE bit of register 9h is set to 1, the day will be ignored, and an interrupt occurs ones the actual time matches the seconds, minutes and hour setting of the alarm register.

(Example) Write 80h (AE = 1) to the WEEK Alarm / DAY Alarm register (Reg - 9h):

Only the hour, minute and second settings are used as alarm comparison targets. The week and date settings are not used as alarm comparison targets.

As a result, alarm occurs if only the hour, minute and second values match the alarm data.

If all 4 AE bit values are 1 the week/date and time settings are ignored, and an alarm interrupt event will occur once per second.

The alarm does not occur even if it is set the same as the current time. Occurs at the next time match.

2) WADA bit (Week Alarm / Day Alarm Select)

The alarm interrupt function uses either Day or Week as its target. The WADA bit is used to specify either WEEK or DAY as the target for alarm interrupt events.

Table 29 WADA bit	(Week Alarm / Day Alarm Select)	

WADA	Data	Description
	0	Sets WEEK as target of alarm function. Sunday from Monday.
Write	1	Sets DAY as target of alarm function. 1day to 31day.

3) AF bit (Alarm Flag)

When this flag bit value is already set to 0, occurrence of an alarm interrupt event changes it to 1. When this flag bit value is 1, its value is retained until a 0 is written to it. Table 30 AE bit (Alarm Elag)

AF	Data Description							
Write	0	Clearing this bit to zero enables /INT low output to be canceled (/INT remains Hi-z) when an alarm interrupt event has occurred.						
	1	Invalid (writing a 1 will be ignored)						
	0	Alarm interrupt events are not detected.						
Read	1	Alarm interrupt events are detected. (Result is retained until this bit is cleared to zero.)						

4) AIE bit (Alarm Interrupt Enable)

This bit is used to control output of interrupt signals from the /INT pin when an Alarm interrupt event has occurred.

	Table 31 AIE bit (Alarm Interrupt Enable)							
AIE	Data	Description						
Write	0	 When an alarm interrupt event occurs, an interrupt signal is not generated or is canceled (/INT status remains Hi-z). When an alarm interrupt event occurs, the interrupt signal is canceled (/INT status changes from low to Hi-z). 						
	1	When an alarm interrupt event occurs, an interrupt signal is generated (/INT status changes from Hi-z to low).						

The AIE bit is only output control of the /INT pin. It is necessary to clear an AF flag to cancel alarm.

14.3.2. Examples Of Alarm Settings

1) Example of alarm settings when Week has been specified (and WADA bit = 0)

Table 32 Alarm Setting Ex1.											
			W	eek	Alaı	m					
Week is specified WADA bit = 0		bit 6	bit 5				bit 1		HOUR Alarm	MIN Alarm	SEC Alarm
		s	F	т	w	т	М	s			
Monday through Friday, at 7:00 AM Second value is ignored. Alarm repeatedly generate for 1 minute at set time.	0	0	1	1	1	1	1	0	07h	00h	AE bit 1
Every Saturday and Sunday, for 30m00s each hour Hour value is ignored	0	1	0	0	0	0	0	1	AE bit 1	30h	00h
Every day, at 6:59:30 PM		1	1	1	1	1	1	1	18h	59h	30h
		Х	Х	Х	Х	Х	Х	Х	1011	5911	5011

X: Don't care

2) Example of alarm settings when Day has been specified (and WADA bit = 1)

Table 33 Alarm Setting Ex2.											
			D)ay /	Alarr	n					
Day is specified	bit	bit	bit	bit	bit	bit	bit	bit	HOUR	MIN	SEC
WADA bit = 1		6	5	4	3	2	1	0	Alarm	Alarm	Alarm
		•	20	10	80	04	02	01			
First of each month, at 7:00 AM Second value is ignored. Alarm repeatedly generate for 1 minute at set time.	0	0	0	0	0	0	0	1	07h	AE bit 1	AE bit 1
15 th of each month, for 30m00s each hour Hour value is ignored	0	0	0	1	0	1	0	1	AE bit 1	30h	00h
Every day, at 6:59:30 PM	1	х	х	х	х	х	х	х	18h	59h	30h

X: Don't care

14.3.3. Diagram Of Alarm Interrupt Function



Figure 24 Alarm Interrupt Black Diagram



Figure 25 Alarm Interrupt Timing Chart

14.4. Time Update Interrupt Function

The time update interrupt function generates interrupt in one-second or one-minute intervals which are synchronized to the update of the second or minute time register of the RTC When an interrupt event is generated, This /INT status is automatically cleared (/INT status changes from low level to Hi-z earliest 7.57 ms after the interrupt occurs).

14.4.1. Related Registers For Time Update Interrupt Functions.

Bank1 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Dh	Extension Register	FSEL1	FSEL0	USEL	TE	WADA		TSEL1	TSEL0
Eh	Flag Register	POR	z	UF	TF	AF	EVF	VLF	XST
Fh	Control Register	z	z	UIE	TIE	AIE	EIE	z	STOP

Table 34 Time Update Interrupt Registers

Before entering settings for operations, it is recommended to first set the UIE bit to 0 in order to avoid inadvertent hardware interrupt at setting.

When the STOP bit value is 1 time update interrupt events do not occur.

Although the time update interrupt function cannot be fully stopped, if 0 is written to the UIE bit, the time update interrupt function can be prevented from changing the /INT pin status to low.

1) USEL bit (Update Interrupt Select)

This bit is used to select second update or minute update as the timing for generation of time update interrupt events.

Table 35 USEL bit (Update Interrupt Select)

USEL	Data	Description
Write	0	Selects second update (once per second) as the timing for generation of interrupt events
vvnie	1	Selects minute update (once per minute) as the timing for generation of interrupt events

2) UF bit (Update Flag)

This flag bit value changes from 0 to 1 when a time update interrupt event occurs.

Table 36 UF bit (Update Flag)

UF	Data	Description	
Write	0	Clearing this bit to zero enables /INT low output to be canceled (/INT remains Hi-z) when an time update interrupt event has occurred.	
	1	Invalid (writing a 1 will be ignored	
	0	Time update interrupt events are not detected.	
Read	1	Time update interrupt events are detected. (The result is retained until this bit is cleared to zero.)	

3) UIE bit (Update Interrupt Enable)

This bit selects whether to generate an interrupt signal or to not generate it.

Table 37 UIE bit (Update Interrupt Enable)

UIE	Data	Description
Mille / Deed	0	 Does not generate an interrupt signal when a time update interrupt event occurs (/INT remains Hi-z) Cancels interrupt signal triggered by time update interrupt event (/INT changes from low to Hi-z).
Write / Read	1	 When a time update interrupt event occurs, an interrupt signal is generated (/INT status changes from Hi-z to low). 7.57ms after the interrupt occurs, the /INT status is automatically cleared (/INT status changes from low to Hi-Z).




Figure 27 Time Update Timing Chart

14.5. Status Monitoring Function

It is a flag bit that detects the state of this product and holds the result. 3 kinds of status changes.

- Power ON Reset
- VLF bit is set
- XST bit is set.

14.5.1. Related Registers For Status Monitoring.

Table 38 RTC Status Monitor Register

Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank1 - E	Flag Register	POR	z	UF	TF	AF	EVF	VLF	XST

1) POR bit

Detects Power-on Reset (POR) occurred.

Table 39 POR bit (Power ON Reset)

POR	Data	Description			
Write	0	Clear for next detection.			
vvnie	1	Ignored.			
	0	POR was not detected.			
Read	1	POR was detected. (The result is retained until this bit is cleared to zero.) The default value of the register is set by power-on reset.			

2) VLF bit

VLF are set from POR or XST.

Table 40 VLF bit (Voltage Low Flag)

VLF	Data	Description
Write	0	Clear for the next detection.
white	1	Ignored
	0	VLF was not detected.
Read	1	POR or XST was detected. (The result is retained until this bit is cleared to zero.) It is used for judgment of initialization of an RTC.

3) XST bit

When an oscillation of crystal is stopped, it is set.

Table 41 XST bit (X'tal Oscillation Stop)

XST	Data	Description				
Write	0	Clear for the next detection.				
white	1	Ignored.				
	0	XST was not detected.				
Read	1	Crystal oscillation stop was detected. (The result is retained until this bit is cleared to zero.)				

This bit is not initialized in power-on reset.

14.6. FOUT Function [Clock Output Function]

The clock signal can be output via the FOUT pin. Output is stopped upon detection of the voltage drop below When the output of an FOUT terminal was stopped, a FOUT shifts to Hi-z

14.6.1. FOUT Control Register

Table 42 FOUT Register (Frequency OUT)									
Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank1 - D	Extension Register	FSEL1	FSEL0	USEL	TE	WADA		TSEL1	TSEL0

14.6.2. FOUT Function Table

1) FSEL1, FSEL0 bit

Table 43	FSEL	Register	(Frequenc	v Select)
	1 OLL	register	(i requeile	,

			3 1 1 1 1		
FSEL1	FSEL0	TMPIN	Output		
0	0	х	32768 Hz Output		
0	1	0	1024 Hz Output		
1	0	0	1 Hz Output		
1	1	х	OFF		

X: don't care

Timer interrupt output can be assigned to the FOUT pin, so when using frequency output, set TMPIN = 0 and set the timer interrupt to the /INT pin.

At the time of the initial power-on, 0 is set to FSEL1, FSEL0.

Note: The effect of STOP bit to FOUT functions.

When STOP = 1, 32768 Hz and 1024 Hz output is possible. But 1 Hz output is disabled.

14.7. Battery Backup Switchover Function

14.7.1. Description of Battery Backup Switchover Function

This function can detect voltage drop of V_{DD} and switchover power supply from V_{DD} to V_{BAT}. This function circuit comprises the comparator detector VDET which detect the power down of the main power source V_{DD}, and built-in MOS switch (SW) and a diode located between the main power-source pin V_{DD} and the backup power supply pin V_{BAT}. Refer to Figure 28.

By switching SW according to the result of the supply-voltage detection of VDET1, the RTC power supply is changed from V_{DD} . Also, the diode protects reverse current from V_{BAT} to V_{DD} .

There are two modes depend on power supply status.

- 1) Normal mode: RTC power supply from VDD
- 2) Backup mode: RTC power supply from V_{BAT}

During backup mode, FOUT becomes Hi-Z status, SPI-Bus is inactive, signal lines are floating.

When the VLF bit detects $0 \rightarrow 1$, the default value of backup battery switchover function related registers is set.



Figure 28 Battery Backup Switchover Function Block Diagram

14.7.2. Related Register of Battery Backup Switchover Function

Table 44 Battery backup switchover function related register

Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank3 - 2	Power Switch Control		INIEN	z	z	SWSEL1	SWSEL0	SMPT1	SMPT0

1) INIEN bit

Control of MOS-Switchover function ON/OFF.

Table 45 INIEN bit (Initial Enable)

INIEN	Data	Description
	0	MOS switchover control function: OFF Default setting.
Write / Read	1	MOS switchover control function: ON If V_{DD} voltage drop is detected SPI-Bus communication is switched OFF and signals are floating.

2) SW status

Table 46 SW status						
State	SW	Description				
Power supplied from VBAT first then VDD supply	OFF	Power supplied diode OR of V_{DD} and V_{BAT} .				
Power supplied from VDD first then VBAT supply	OFF	Power supplied from V_{DD} via diode first then Power supplied diode OR of V_{DD} and V_{BAT} .				
Battery backup switchover function: ON	ON	V _{DD} = ON: Normal mode				
INIEN bit = 1	OFF	V _{DD} = OFF: Backup mode				

3) SWSEL1, SWSEL0 bit

When user set INIEN to 0, it is locked status of a built-in MOS switch

INIEN	SWSEL1	SWSEL0	SW	SPI disable control	comment		
	0	1	OFF	OFF	Default		
0	1	0	ON	OFF	Battery backup switchover function: OFF		
0	0 0		OFF	OFF	Do not select this combination		
	1	1	OFF	OFF	Do not select this combination		
1	1	1 1		ON	SPI-Bus interface: ON		
	Other than (1,1)		Auto control	ON	Battery backup switchover function: ON		

Table 47 INIEN, SWSEL combination

When using a non-re-chargeable battery, it is necessary to install a charge protection diode externally.



Figure 29 Battery backup switchover control (Initial power on)

Voltage detection intermittent timing of VDD

Table 48 The timing of VDET							
Power supply	V _{DD} (INIEN=1)	V _{DD} (INIEN=0)	VBAT (Backup mode)				
VDET detection	Always ON	Stopped	Once per 31.25 ms				



(In case of long period SW=OFF, if V_{DD} power shuts down RTC loses power supply. Careful control is needed for SW=OFF period.

Figure 30 Battery backup switchover control (INIEN:1)

4) SMPT1, SMPT0 bit

7) V_{DD} voltage detection register SMPT1, SMPT0 bit Battery switchover functions managed by V_{DD} voltage low detection (-V_{DET1}).

This detection is checking voltage anytime with setting SW($V_{DD} \sim V_{BAT}$) ON/OFF intermittently.

These two bits control SW OFF period and user can check much precision voltage by preventing reverse current from V_{BAT} to V_{DD} when main V_{DD} shuts down.

V_{DD} voltage low detection (-V_{DET1}) is active anytime, so lower voltage detection moves RTC into backup mode immediately regardless SW OFF time.

These SW OFF occur every second. Refer to Figure 31

SMPT1	SMPT 0	SW OFF time
0	0	Always ON
0	1	2 ms
1	0	128 ms
1	1	256 ms

Table 49 SMPT bit (sample time)

Once per a Second.



Note in using small EDLC.



Figure 32 Battery Management for small EDLC

14.8. Time Stamp Function

14.8.1. Description Of Time Stamp Function

Time stamp function is executed by two kinds of event.

1) Command trigger of SPI-Bus communication by Bank2 Fh reading.

2) RTC self monitoring warning.

The time stamp records maximum 8-events. Also interrupt output is available with /INT pin. This time stamp function works even in backup mode and records time data from 1/256 s to year.



Figure 33 Time Stamp function

14.8.2. Related Registers For Time Stamp Functions.

		Tal	ole 50 Time	e Stamp fui	nction regi	sters			
Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank1- D	Extension Register	FSEL1	FSEL0	USEL	TE	WADA		TSEL1	TSEL0
Bank1 E	Flag Register	POR	0	UF	TF	AF	EVF	VLF	XST
Bank1 F	Control Register	z	z	UIE	TIE	AIE	EIE	z	STOP
Bank2 B	Over Write Control			١	lo Functio	n		OVW	-
Bank2-E	Time Stamp control 0	z	z	z	z	z	z	z	COMTG
Bank2-F	Command Trigger	z	z	z	z	z	z	z	z
Bank3-4	Time Stamp Control 1	z	z	z	z	z	EISEL	TSCLR	TSRAM
Bank3-5	Time Stamp Control 2	•	z	z	z		EVDET		EXST
Bank3-6	Time Stamp Control 3	z	z	z	TSFUL	TSEMP	TSAD2	TSAD1	TSAD0

51) EVF bit (Event Flag)

When event occurs, a Time stamp is performed, and EVF is set.

Table 51 EVF bit (Event Flag)

EVF	Data	Description
Write	0	When /INT is outputting Low, it is canceled. It is released to Hi-Z.
white	1	Ignored
	0	Specified interrupt events are not detected.
Read	1	Event occasion is detected. (The result is retained until this bit is cleared to zero.)

Note: EVF is not set by SPI-Bus command trigger

2) EIE bit (Event Interrupt Enable)

EIE can control INT outputs of event interruption.

Table 52 EIE bit (Event Interrupt Enable)

EIE	Data	Description
Write	0	 When an event interrupt event occurs, an interrupt signal is not generated (/INT status remains Hi-z) When an event interrupt event occurs, the interrupt signal is canceled. (/INT status changes from low to Hi-z)
	1	When an event interrupt occurs, an interrupt signal is generated (/INT status changes from Hi-z to low)

3) OVW bit (Over Write)

Control of overwriting of Time stamp record

Table 53 OVW bit (Over Write)

OVW	Data	Description
))//rite	0	The recording is stopped with 8-time stamps, and it is not overwritten.
Write	1	Overwrite available

Address Bank3 6h



Figure 34 OVW, pointer operation

14.8.3. Time Stamp function triggered by SPI Access

 COMTG bit (Command Trigger) Time stamp by SPI-Bus access. Note: EVF is not set by SPI-Bus command trigger. Therefore, Time stamp interruption doesn't occur. This function was prepared for to read time data of sub seconds from Year without contradiction.

		Table 54 COMTG bit (Command Trigger)
COMTG	Data	Description
	0	Time stamp by SPI-Bus is disabled.
Write	1	Time stamp by SPI-Bus available When a reading command to Bank2 address Fh is transmitted by SPI-Bus, the time is recorded by Bank2 address 0h to 9h. The read value of Bank2 address Fh is 0h.

2) Time stamp Timing

CLK	
DI) 1) 1) 1) 1) Dummy read
	Mode + Address(Ah + Fh)
	¥
Time stamp trigge	r∱Trigger
Time stamp trigge /INTpin	r↑Trigger/

Figure 35 Time Stamp SPI-Bus record timing

14.8.4. Time Stamp Record Register.

When an event is detected, the following data is recorded .



Multiple access time stamp data is available. Refer to Figure 33.

address	bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0
Bnak2 0h							1/512	1/1024
Bank2 1h	1/2	1/4	1/8	1/16	1/32	1/64	1/128	1/256
address	bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0

Figure 36 Time stamp recording registers

Tahlo	55	Time	Stamn	Record	Register
Iable	22	IIIIe	Stamp	Record	register

Bank2 Address	Function	Time stamp data
0h	Time Stamp 1/1024S	256Hz,512Hz.
1h	Time Stamp 1/128S	1Hz~256Hz
2h	Time Stamp SEC	Seconds
3h	Time Stamp MIN	Minutes
4h	Time Stamp HOUR	Hours
5h	Time Stamp WEEK	Day
6h	Time Stamp DAY	Date
7h	Time Stamp MONTH	Month
8h	Time Stamp YEAR	Years
9h	Status Stamp	RTC Internal status (VDET, XST)

Status stamp register

			Та	ble 56 Sta	tus Stamp				
Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Bank2 – 9h	Status Stamp	z	z	•	•	VDET	z	XST	z

Table 57 Time Stamp RAM control registers

Bank3 Address [h]	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
4	Time Stamp Control 1	z	z	z	z	z	EISEL	TSCLR	TSRAM
5	Time Stamp Control 2	•	z	z	z	•	EVDET		EXST
6	Time Stamp Control 3	z	z	z	TSFUL	TSEMP	TSDA2	TSDA1	TSDA0

14.8.4. RTC Self Monitoring Time stamp Function

1) VDET bit (Time Stamp VDET) Comparison result of VDD and VDET1

Table 58 VDET bit

VDET	Data	Description
Read	0	V _{DD} > V _{DET1} , Normal mode (V _{DD} supply)
	1	V _{DD} < V _{DET1} , Backup mode (V _{BAT} supply)

XST bit (Time stamp X'tal Oscillation Stop) 2) Status record of crystal oscillation

oladoro	Table 59 XST bit					
XST	Data	Description				
	0	Crystal oscillation is normal.				
Read	1	Crystal oscillation stopped or temporarily stopped. XST detects more than 10ms stopped.				

The time stamp cannot be recorded at the moment of oscillation stop. It is recorded at the moment the oscillation restores.

3) EVDET bit (Enable VDET)

EVDET DIT (Enable VET) Enable/Disable control of time stamp VDET Table 60 EDVET bit

EVDET	Data	Description					
Write	0	No time stamp even VDET is detected.					
	1	Time stamp by VDET detection.					

EXST bit (Enable Time stamp X'tal Oscillation Stop) 4) Enable/Disable control of time stamp XST

		Table 61 EXST bit					
EXST	Data	Description					
Read	0	No time stamp even Crystal oscillation stops.					
	1	Time stamp by Crystal oscillation stop detection.					

14.8.5. Time Stamp Record Register

When an event is detected, the following data is recorded.

		Table	e 62 Time S	Stamp RAM	l control re	gisters			
Bank3 Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
4h	Time Stamp Control 1	z	z	z	z	z	EISEL	TSCLR	TSRAM
5h	Time Stamp Control 2	•	z	z	z	•	EVDET		EXST
6h	Time Stamp Control 3	z	z	z	TSFUL	TSEMP	TSDA2	TSDA1	TSDA0



Figure 37 Careful timing process for VDET, XST time stamp

14.8.6. Multiple Time Stamp

By using following registers, user can record time stamp maximum 8-times.

Multiple timestamp related register Multiple time stamp operation is possible by setting the following registers. 1/1024 seconds and WEEK information are not recorded in the recording area of Bank4 ~ Bank7.

1) TSRAM bit (Time Stamp RAM)

Selection of time stamp recording area or USER RAM.

		Table 63 TSRAM bit (Time Stamp RAM)			
TSRAM	M Data Description				
	0	It can read and write as USER RAM. Time stamp data is recorded only at addresses Bank2 0h to 8h.			
Write	1	Bank4 to Bank7 is used as the time stamp recording area. To clear the time stamp data, write 0 directly to the recording area by SPI-Bus access.			

When TSRAM = 1, the first time stamp is recorded in both Bank2 0h \sim 8h and Bank4 0h \sim 7h.

		pointer	Address (h)	Bit7 ~ bit0
Time Stemp	ſ	0,0,0	Bank4 0~7h	Time stamp data 1
Time Stamp Events 3-times	-	0,0,1	Bank4 8~Fh	Time stamp data 2
Lvents 5-times	l	0,1,0	Bank5 0~Fh	Time stamp data 3
		0,1,1	Bank5 8~Fh	
		1,0,0	Bank6 0~7h	
		1,0,1	Bank6 8~Fh	
USER RAM	ſ	1,1,0	Bank7 0~Fh	Data xx
2bytes use	1	1,1,1	Bank7 8~Fh	Data yy

Figure 38 Mixed usage of USER RAM and Time stamp RAM

2) TSCLR bit (Time Stamp Clear) Initialization of Bank3 6h

Table 64 TSCLR bit

TSCLR	Data	Description
	0	No operation
Write	1	Initialize Bank3 6h. TSEMP: 1, TSFUL: 0, TSAD2,1,0: (1,1,1)

3) EISEL bit (Enable Interrupt Select)

Enable/Disable control of interrupt is output when 8-time stamp data becomes full.

Table 65 EISEL bit (Event Interrupt Select)

EISEL	Data	Description
) A (rite	0	Each event makes interrupt output respectively from /INT.
Write	1	In case of 8-time stamp full recording, interrupt output from /INT.
Even SPI-Bus	command tri	ager is executed, it makes no interrupt output

Even SPI-Bus command trigger is executed, it makes no interrupt output.

1) TSFUL bit (Time Stamp Full) 8-time stamp data area full recording

Table 66 TSFUL bit					
TSFUL	Data Description				
Deed	0	Time stamp RAM area is not full.			
Read	1	8 times of time stamp recording area is fully recorded.			

2) TSEMP bit (Time Stamp Empty) No recording date in RAM.

Table 67 Time Stamp Empty bit					
TSEMP	Data	Description			
Read	0	There is some data.			
	1	There is no data.			

TSAD2, TSAD1, TSAD0 bit (Time Stamp Address pointer) The latest address pointer time stamped recorded in RAM

T - 1, 1 -	~~	-	1. 14
i abie	68	TSAD	DIT

TSAD2, 1, 0	TSAD2	TSAD1	TSAD0	Address pointer
	0	0	0	Bank4 0h - 7h
	0	0	1	Bank4 8h - Fh
	0	1	0	Bank5 0h - 7h
_ .	0	1	1	Bank5 8h - Fh
Read	1	0	0	Bank6 0h - 7h
	1	0	1	Bank6 8h - Fh
	1	1	0	Bank7 0h - 7h
	1	1	1	Bank7 8h - Fh, default

Figure 39 Multiple time stamp recording

14.9. Flow Chart

The following flow-chart is one example, but it is not necessarily applicable for every use-case and not necessarily the most effective process for individual applications.

1) In Initial power on



Figure 40 Flow1

2) Initialize



Figure 41 Flow2

Example 2. Initialization example when using only clock function.



Figure 42 Flow3

3) The setting of the clock and calendar



- Set STOP bit to "1" to prevent time update in time setting.
- Write information of [year / month /date [day of the week] hour: minute: second] which is necessary to set (or reset). In case of initialization, please initialize all data.
- Cancel STOP bit to "0" and start (restart) clock movement. Clock is started when set STOP bit to "0".
- * It is able to set time even if not combined use of STOP bit. If do not use the STOP bit, RTC will start counting from the point of writing second. Even when batch writing is performed from [seconds] to [year], the counter below second will be reset by the acknowledge following [s], clocking will start from that point.
- * When STOP = 1, please be aware that the functions such as the voltage detection function stop.

Figure 43 Flow4

4) The reading of the clock and calendar



Figure 44 Flow5

5) Setting example of the Wake-up timer interrupt function



Figure 45 Flow6

RX4111CE

6) Setting example of the Alarm interrupt function



Figure 46 Flow7

7) One shot timestamp function setting example



Figure 47 Flow8

4.10. Reading/Writing Data via the SPI-Bus Interface

First for both read and write, input High from Low to CE. Then specify the 4-bits address, and finally read or write in 8bits units. Both read and write use MSB-first. In continuous operation, objected address is auto incremented. Auto incrementing of the address is cyclic, so address Fh is followed by address 0.

14.10.1 Write / Read and Bank Select

R/W and Register bank are specified by the four bits mode setting code.

-			-	
Mode	Bank1	Bank2	Bank3	Bank6
Read	9h	Ah	Bh	Eh
Write	1h	2h	3h	6h

Bank5 and Bank6 are for software reset

14.10.2 Write of Data

One-shot writing



2) Continuous writing



When writing data, the data needs to be entered in 8-bits units.

If the input of data in 8-bits unit is not completed before CE input falls, the 8-bits data will not be written properly at the time CE input falls.

14.10.3 Read of Data

¹⁾ One-shot reading



15.Circuit Diagram Connection



Figure 48 Typical MCU connection example

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